

FEATURES

- 45 mΩ High-Side MOSFET
- 0.5~4.0 A (typ.) Adjustable Current Limit
- 6.0mA Average Current in OUT shorted GND
- Support Apple® Devices fast charging (Apple® 2.1A / 2.4A mode)
- Support Samsung Galaxy Tab Devices fast Charging
- Support BC1.2 & YD/T 1591-2009 Charging Spec
- Linear Current sense of Output Current.
- Built-in Soft-Start
- Support single layer PCB layout.
- 4.5 ~ 6.5V Single Supply Operation.
- Available EMSOP8, ESOP8 package.

APPLICATIONS

- USB Charger
- USB Wall Adapter
- Car Charger

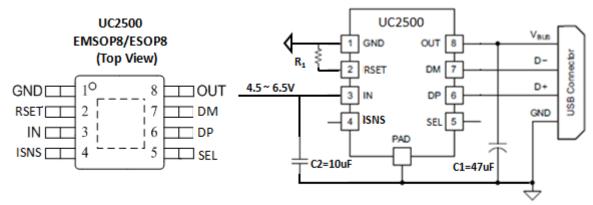
DESCRIPTION

The UC2500 integrated USB charger emulators with automatic host charger identification circuitry and high performance adjustable current limiting power switch. An automatic USB charger identification circuit allows mobile power supply can automatically provides the correct modes on the data lines to charger compliant devices among the Apple, Samsung and BC1.2 modes.

The UC2500 is a $45 m\Omega$ power switch intended for applications where heavy capacitive loads and short-circuits are likely to be encountered. This also provides hiccup mode when OUT voltage is less than 1.8V or OTSD.

The UC2500 provides a ISNS pin for current sense or USB cable resistance compensation and an SEL pin to select 10W or 12W mode in application.

PACKAGE AND APPLICATION



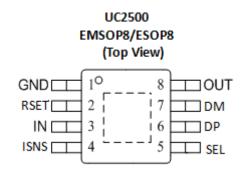
SEL = 0: Apple=2.4A, SS=2A, DCP=1.5A; SEL = 1 or Floating: Apple=2.1A, SS=2A, DCP=1.5A; ISNS is floating or pull up with 10k Resistor if not used

ORDING INFORMATION

Part Number	Package Type	Package Qty	Op Temp(°C)	Mark
UC2500	EMSOP8	3000	40.05	UC2500
	ESOP8	3000	-40~85	XXX



PINOUT

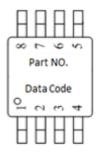


PIN FUNCTIONS

NO.	NAME	TYPE ⁽¹⁾	DESCRIPTION
1	GND	G	Ground connection
2	RSET	I	External resistor used to set current-limit threshold;
3	IN	P/I	Power supply/Input voltage connected to Power Switch; connect a 1 µF or greater ceramic capacitor from IN to GND as close to the IC as possible
4	ISNS	0	Current Sense of OUT current, the current sense ratio is 39uA/A;
5	SEL	I	Logic-level control input; When it is high or floating, DP/DM operate in 2.1A mode, when it is Low, DP/DM operate in 2.4A mode;
6	DP	O/I	DP date line to connector, output for hand-shake voltage to portable equipment, high impedance while disabled
7	DM	O/I	DM data line to connector, input for hand-shake voltage from portable equipment high impedance while disabled
8	OUT	0	Power-switch output, connected to VBUS of USB; connect a 22µF or greater ceramic capacitor from OUT to GND as close to the IC as possible

⁽¹⁾ G = Ground, I = Input, O = Output, P = Power

MARK INFORMATION





ABSOLUTE MAXIMUM RATINGS (1)

Over recommended operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT		
Supply Voltage Range	IN	-0.3	7.0	V	
Input voltage range	DP,DM	-0.3	5.8		
Continuous output sink current	DP input current, DM input current		35	mA	
Continuous output source current	DP output current, DM output current		35		
ESD rating, Human Body	IN		2	kV	
Model (HBM)	DP, DM		2	KV	
Operating Junction Temperature	TJ	-40	125		
Storage Temperature Range	T _{stg}	-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC			
θ_{JA}	EMSOP8 Package thermal impedance ⁽¹⁾	65	°C/W
OJA	ESOP8 Package thermal impedance ⁽¹⁾	42	O, VV

⁽¹⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS

	PARAMETER	MIN	MAX	UNIT
V _{IN}	Input voltage of IN	4.5	6.5	V
V _{DP/DM}	DP data line input voltage		5.5	ď
I _{DP/DM}	Continuous sink/source current		±10	mA
R _{SET}	Resistance of R _{SET}	13	100	kΩ
I _{OUT}	Continuous sink/source current	500	4000	mA
TJ	Operating Junction Temperature	-40	125	°C



ELECTRICAL CHARACTERISTICS

Conditions are: TA = 25° C, VIN = 5.0 V, VSEL = VIN and RSET = $19.1 \text{ k}\Omega$. Positive current are into pins. All voltages are with respect to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Power Switch						
Б	EMSOP8 Package			45	68	0
RDSON	ESOP8 Package	I _{OUT} =1A		55	83	mΩ
Current Limit						
	OUT assessed livelies d	Rset=19.1k	2.45	2.74	3.03	_
los	OUT current limited	Rset=21.5k	2.16	2.43	2.70	A
Hiccup Mode	•					•
Vout_short	OUT Threshold Voltage to enter Hiccup mode		1.3	1.50	1.7	V
Ton_HICCUP	ON Time of Hiccup mode		11	22	33	ms
Toff_HICCUP	OFF Time of Hiccup mode		5	11.5	18	s
Current Sense						
		IOUT=3.0A		117		
Ics	OUT current sense	IOUT=2.0A		78		uA
		IOUT=1.0A		39		
Bandwidth				600		kHz
Thermal Shutdo	own					
	Temperature Rising Threshold		145	152	160	°C
	Hysteresis			17		



ELECTRICAL CHARACTERISTICS

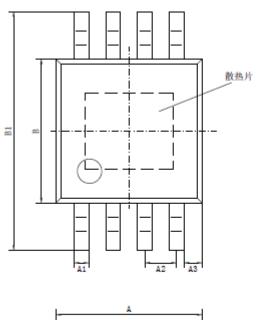
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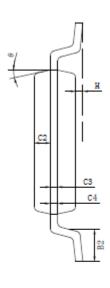
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
UNDERVOLTAGE L	OCKOUT		<u>.</u>			
VuvLo	IN rising UVLO threshold voltage		3.75	3.95	4.15	V
	Hysteresis			100		mV
SUPPLY CURRENT			<u> </u>			
lin	IN supply current			160	280	μA
BC 1.2 DCP MODE	(SHORT)		•			
RDPM_SHORT	DP / DM shorting resistance			125	200	Ω
RDCHG_SHORT	Resistors connected DP /DM to GND after hand-shaking			200	400	kΩ
V _{DPL_TH_DETACH}	DP low threshold while detaching BC1.2 devices		310	330	350	mV
VDPL_TH_DETACH_HYS	hysteresis			50		mV
IPAD MODE 2.1A M	ode (SEL=1 or Floating)					
V _{DP_IPAD}	DP output voltage		2.5	2.7	2.9	V
V _{DM_IPAD}	DM output voltage		1.85	2.0	2.15	V
RDP_IPAD	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
IPAD MODE 2.4A M	ode (SEL=0)					
V _{DP_IPAD}	DP output voltage		2.5	2.7	2.9	V
V _{DM_IPAD}	DM output voltage		2.5	2.7	2.9	V
RDP_IPAD	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
Galaxy Tab MODE						
V _{DP_GAL}	DP output voltage		1.1	1.2	1.3	V
V _{DM_GAL}	DM output voltage		1.1	1.2	1.3	v
R _{DP_GAL}	DP output impedance	I _{DP} = -5uA	65	105	140	140
Rdm_gal	DM output impedance	I _{DM} = -5uA	65	105	140	kΩ

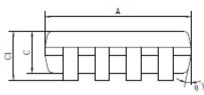


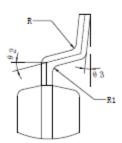
PACKAGE INFORMATION

EMSOP8





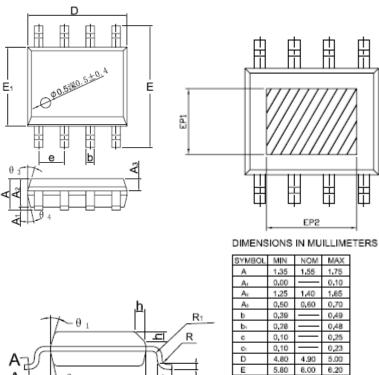


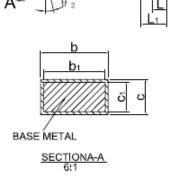


标注 尺寸	最小(==)	最大(mm)	标注	最小(==)	最大(mm)	
A	2.90	3.10	C3	0.	152	
A1	0.28	0.35	C4	0.15	0.23	
A2	0.6	5TYP	H	0.02	0.15	
A3	0.3	75TYP	θ	12	° TYP4	
В	2.90	3.10	0 1	12° TYP4		
B1	4.70	5. 10	0.2	14	° IYP	
B2	0.45	0.75	03	o	`~ 6°	
C	0.75	0.95	R	0.	15TYP	
C1	-	1.10	R1	0. 15TYP		
C2	0.3	28TYP				
* 注: EMSO	P8产品框架基岛尺寸为:	1.80X1.80, 散热片尺寸	为1.80X1.55	(单位: mm)		



ESOP8





A	1,35	1.55	1.75
Aı	0.00		0.10
Acc	1,25	1.40	1.65
A ₀	0,50	0,60	0.70
ь	0,39	_	0,49
b _i	0,28		0,48
e	0,10	_	0,25
01	0,10	_	0,23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E ₁	3.80	3.90	4.00
6	1	.27BSC	
L	0.45	_	1.00
L	_	,04REF	
Lı	- ().25BSC	;
R	0,07		
R _i	0,07	_	
h	0,3	0,4	0,5
	O.		8°
в,	11°	17°	19°
0.	11°	13°	15°
0,	15°	17*	19*
в.	11°	13"	15*
EP1	2.40		
EP2	3.30		